Search Hirl. 1/8/05 Ja. (7pp.)

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	hemt.ti,ab,clm. and InAIN near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:03
L2	1	hemt.ti,ab,clm. and ("In.sub."\$4"Al. sub."\$4"N" "In.sub."\$4"Al.sub. "\$4"N") near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:04
L3	0	("(highadjelectronadjmobilityadjtran sistorhemt).ti.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:58
L4	936	(high adj electron adj mobility adj transistor hemt).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:58
15	51	(high adj electron adj mobility adj transistor hemt).ti. and GaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:59
L6	2078	((257/192) or (257/194) or (257/195) or (438/285) or (438/590)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 15:02
L7	1685	6 and (high electron adj mobility adj transistor hemt)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR.	OFF	2005/01/08 15:03
L8	159	6 and (high electron adj mobility adj transistor hemt) and GaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 15:05
L9	7	6 and (high electron adj mobility adj transistor hemt) and GaN and InAIN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 15:07
L10		6 and (high electron adj mobility adj transistor hemt) and GaN and InAlN near8 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/08 15:10

	T			T	1	
L11	71	(("3,764,865") or ("3,767,984") or ("3,855,690") or ("3,861,024") or ("3,943,622") or ("4,030,942") or ("4,075,652") or ("4,157,556") or ("4,163,984") or ("4,173,764") or ("4,325,181") or ("4,424,525") or ("4,593,301") or ("4,642,879") or ("4,714,948") or ("4,980,731") or ("4,961,194") or ("5,041,393") or ("5,021,857") or ("5,041,393") or ("5,180,681") or ("5,192,987") or ("5,180,681") or ("5,192,987") or ("5,312,765") or ("5,352,909") or ("5,358,878") or ("5,359,220") or ("5,365,080") or ("5,411,914")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 15:10
S1	5	"772673".ap.	US-PGPUB;	OR	OFF	2005/01/06 16:14
	1 1 1 1 T		USPAT;			
			EPO; JPO;			
			DERWENT; IBM_TDB			
S2	33	(("5,447,874") or ("5,471,077") or	US-PGPUB;	OR	OFF	2005/01/06 16:17
		("5,486,705") or ("5,493,136") or ("5,521,403") or ("5,521,404") or ("5,554,865") or ("5,596,211") or ("5,611,955") or ("5,652,440") or ("5,668,387") or ("5,698,900") or ("5,739,558") or ("5,811,843") or ("5,811,844") or ("5,821,825") or ("5,831,277") or ("5,834,796") or ("5,847,414") or ("5,856,217") or ("5,900,653") or ("5,929,467") or ("5,976,920") or ("6,049,091") or ("6,049,097") or ("6,049,091") or ("6,049,097") or ("6,140,169") or ("6,177,685") or ("6,214,678")).PN.	USPAT		Table Street	233,01,00 10.17
S3	16	(("6,232,624") or ("6,242,293") or	US-PGPUB;	OR	OFF	2005/01/06 16:19
		("6,242,766") or ("6,316,793") or ("6,355,951") or ("6,392,253") or	USPAT			
		("6,429,467") or ("6,444,552") or				
		("6,465,289") or ("6,515,316") or				
		("6,524,899") or ("6,531,718") or ("6,583,454") or ("6,646,293") or				
	(A)	("6,727,531") or ("20010020700")).				
		PN.				
S4	4	JP-2000223697\$-\$.did.	US-PGPUB;	OR	OFF	2005/01/06 16:29
		JP-2001196575\$-\$.did. wo-0059084\$-\$.did.	USPAT; EPO; JPO;			
		The course of praidi	DERWENT; IBM_TDB			
<u> </u>	L			اـــــــــــــــــــــــــــــــــــــ		

65	T	2000500044 4 111	LIC DODLID		055	2005/04/05 45 24
S5	0	wo-000059084\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:24
S6	1	wo-200059084\$-\$.did.	US-PGPUB;	OR	OFF	2005/01/06 16:21
			USPAT; EPO; JPO;			
		· · · · · · · · · · · · · · · · · · ·	DERWENT;			
العادات والإسادة	「 Mid-interpretation transcore to the co	The second of th	IBM_TDB			The best of the control of the contr
S7	0	(2001/0020700).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:30
S8	2	("20010020700").PN.	US-PGPUB;	OR	OFF	2005/01/06 16:31
			USPAT; EPO; JPO;			
			DERWENT;			
			IBM_TDB			
S9	54	S2 S3 S4 S5 S6 S7 S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 16:32
S10	1645	hemt.ti,ab,clm.	US-PGPUB;	OR	OFF	2005/01/06 17:38
			USPAT; EPO; JPO;			
		[발송] 그렇게 얼룩하는 기울이다	DERWENT;			
			IBM_TDB	:		
S11	1	hemt.ti,ab,clm. and barrier adj layer near4 (InAlN "In.sub."\$3"Al.sub. "\$3"N" "Al.sub."\$3"In.sub."\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 17:39
S12	1	hemt.ti,ab,clm. and barrier adj layer	US-PGPUB;	OR	OFF	2005/01/06 17:40
		near4 (AlInN InAlN "In sub."\$3"Al. sub."\$3"N" "Al.sub."\$3"In.sub.	USPAT; EPO; JPO;			
		"\$3"N")	DERWENT;			
			IBM_TDB			
S13	1	(high adj mobility adj electron adj transistor hemt).ti,ab,clm. and barrier adj layer near4 (AlInN InAlN "In.sub."\$3"Al.sub."\$3"N" "Al.sub. "\$3"In.sub."\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/06 17:40
S14	1	(high adj mobility adj electron adj	US-PGPUB;	OR	OFF	2005/01/06 17:41
		transistor hemt).ti,ab,clm. and (separat\$3 barrier) adj layer near4	USPAT; EPO; JPO;			
		(AlInN InAlN "In.sub."\$3"Al.sub.	DERWENT;			
		"\$3"N" "Al.sub."\$3"In.sub."\$3"N")	IBM_TDB			ens (

· ·	Υ	T	1	Γ	T	7
S15	1	(high adj mobility adj electron adj	US-PGPUB;	OR	OFF	2005/01/06 17:41
		transistor hemt).ti,ab,clm. and	USPAT;			
		(separat\$3 barrier) adj (layer film)	EPO; JPO;		İ	
		near4 (AlInN InAlN "In.sub."\$3"Al.	DERWENT;			
	1	sub."\$3"N" "Al.sub."\$3"In.sub.	IBM_TDB			
		"\$3"N")				
S16	54	(US-20010020700-\$).did. or	US-PGPUB;	OR	OFF	2005/01/06 17:56
		(US-6214678-\$ or US-6177685-\$ or	USPAT;			
		US-6140169-\$ or US-6064082-\$ or	JPO;			logi dan et elektrisis.
.,		US-6100542-\$ or US-6057566-\$ or	DERWENT	service of the service of		
		US-6049091-\$ or US-6049097-\$ or	a same company of the same company	manufacture to the second	and the second s	
		US-5976920-\$ or US-5900653-\$ or		:		
		US-5929467-\$ or US-5880491-\$ or				1
		US-5856217-\$ or US-5834796-\$ or				
		US-5847414-\$ or US-5831277-\$ or				
a de la companya de l		US-5811844-\$ or US-5821825-\$ or				
		US-5811843-\$ or US-5698900-\$ or				
		US-5739558-\$ or US-5696387-\$ or				
		US-5652440-\$ or US-5668387-\$ or				
		US-5611955-\$ or US-5596211-\$).				
	27	did. or (US-5521404-\$ or	1 3 3 3 3			
		US-5554865-\$ or US-5521403-\$ or				least es i tà
		US-5486705-\$ or US-5493136-\$ or			1.0	
		US-5471077-\$ or US-5447874-\$ or				
		US-6727531-\$ or US-6646293-\$ or			* 14	
	History History	US-6583454-\$ or US-6524899-\$ or		ar .	7	
		US-6531718-\$ or US-6515316-\$ or				
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		US-6444552-\$ or US-6392253-\$ or				
		US-6355951-\$ or US-6242766-\$ or				
		US-6316793-\$ or US-6242293-\$ or				
		US-6232624-\$).did. or (JP-2000223697-\$ or				
		JP-2000223697-\$ 01 JP-2001196575-\$).did. or				
		(JP-2001196575-\$ or				
		JP-2000223697-\$ or				
		WO-200059084-\$).did.				
647		Mark the state of				
S17	1	(US-20040155260-\$).did.	US-PGPUB	OR	OFF	2005/01/07 09:47
S18	15	(high adj electron adj mobility adj	US-PGPUB	OR	OFF	2005/01/07 09:48
		transistor hemt).ti. and "257"/\$7.				
		ccls.				
S19	93	(high adj electron adj mobility adj	US-PGPUB;	OR	OFF	2005/01/07 09:50
		transistor hemt).ti. and "257"/\$7.	USPAT		0	2000,02,0,05.00
		ccls.				
S20	1035	(257/194).CCLS.	US-PGPUB;	OR	OFF	2005/01/00 14-53
320	1033		USPAT;	.UK	OFF	2005/01/08 14:57
1			EPO; JPO;	4		
			DERWENT;			
			IBM_TDB			
			=			
S21	1	S20 and (InAlN "In.sub."\$3"Al.sub.	US-PGPUB;	OR	ON	2005/01/07 09:54
		"\$3"N" "Al.sub."\$3"In.sub."\$3"N")	USPAT;			
ĺ		and charge adj density	EPO; JPO;			
			DERWENT;			1
			IBM_TDB			

		·				
S22	5	S20 and (InAlN "In.sub."\$3"Al.sub. "\$3"N" "Al.sub."\$3"In.sub."\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:23
S23	1	S20 and (InAlN "In.sub."\$3"Al.sub. "\$3"N" "Al.sub."\$3"In.sub."\$3"N") and (QW quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:24
S24	3	S20 and (InAlN "In.sub."\$3"Al.sub. "\$3"N" "Al.sub."\$3"In.sub."\$3"N") and (2DEG Q2DEG two-dimensional adj electron adj gas two-dimensional adj Fermi adj gas QW quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 10:44
S25	9	(hemt high adj electron adj mobility adj transistor) and (InAlN "In.sub. "\$3"Al.sub."\$3"N" "Al.sub."\$3"In. sub."\$3"N") and (2DEG Q2DEG two-dimensional adj electron adj gas two-dimensional adj Fermi adj gas QW quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 11:00
S26	2	(hemt high adj electron adj mobility adj transistor) and (InAlN "In.sub. "\$3"Al.sub."\$3"In. sub."\$3"N") near6 (barrier separating separation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 11:36
S27	62	(hemt high adj electron adj mobility adj transistor) and (AlGaN "Al.sub. "\$3"Ga.sub."\$3"N" "Ga.sub."\$3"Al. sub."\$3"N") near6 (barrier separating separation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 11:40
S28	19	(hemt high adj electron adj mobility adj transistor) and (AlGaN "Al.sub. "\$3"Ga.sub."\$3"N" "Ga.sub."\$3"Al. sub."\$3"N") near6 (barrier separating separation) and (QW quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:56
S29	22	portable adj telephone.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:57
S30	48	low adj noise adj amplifier.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:54

S31	27	radar.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:57
S32	20	sensor.ti,ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 16:09
\$33	2	direct adj broadcast adj satellite.ti, ab,clm. and HEMT.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S34	1	S29 and S30 and S31 and S32 and S33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S35	1	S29 and S30 and S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S36		S29 and S30 and S31	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S37	1	S29 and S30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 14:59
S38	1	S30 and S31 and S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:55
S39	5	S30 and S31	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:55
S40	8	"intermediate frequency amplifier" and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 16:45

S41	0	"intermediate frequency amplifier" and (intermediate adj amplifier) and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 16:46
S42	8	"intermediate frequency amplifier" and (intermediate adj2 amplifier) and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 16:48
S43	8	"intermediate frequency amplifier" and (intermediate adj2 amplifier IF adj amplifier) and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 16:49
S44	9	(intermediate adj2 amplifier IF adj amplifier) and hemt.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 17:52
S45	4	hemt.ti,ab,clm. and InGaN near4 channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/08 14:02